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/DN/ 10581127 - GAU: 2895 Sheet 1 of 2 **AP20R6C PCT/PTO 30** MAY 2006

FORM PTO-14	149		ATTY DOCKET NO.	SERIAL NO.							
INFORMATION DISCLOSURE STATEMENT			536-009.028	To be assigned 581127							
			APPLICANT: B. HEINEMANN et al.								
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UNITED STATES PATENT DOCUMENTS											
EXAM. INITIAL	DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE					
/ U N/	2005/0023642	Feb. 03, 2005	Heinemann et al.								
***************************************	2003/0146477	Aug. 07, 2003	Krutsick								
9990000	2003/0146468	Aug. 07, 2003	Gris et al.								
COCCCCC	2002/0168829	Nov. 14, 2002	Bock et al.								
/DN/	2003/0162360	Aug. 28, 2003	Beasom		:						
FOREIGN PATENT DOCUMENTS											
(PA)	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO					
/DN/	EP 0 746 038	Dec. 19, 2001	EP								
/DN/	2000188296	July 04, 2000	JP								
/DN/	2000269350	Sept. 29, 2000	JP								
				<u> </u>							
	OTHER DOCUME	NTS (INCLUDING A	AUTHOR, TITLE, DATE, PE	RTINENT	PAGES, ETC.)						
/DN/ 1	M. C. Wilson et al., "Process HJ: A 30 GHz NPN and 20 GHz PNP complementary bipolar process for high linearity RF circuits," IEEE BCTM 9.4, 1998, pp.164-167.										
2	•	D. Knoll et al., "A flexible, low-cost, high performance SiGe:C BiCMOS process with a one-mask HBT module," IEEE, 2002.									
3	B. Heinemann et al.	B. Heinemann et al., "Novel collector design for high-speed SiGe:C HBTs," IEEE, 2002.									
4	D. V. Singh et al., "	D. V. Singh et al., "Novel epitaxial <i>p</i> -Si/ <i>n</i> -Si _{1-y} C _y / <i>p</i> -Si heterojunction bipolar transistors," IEEE, 2000.									
	B. El-Kareh et al., "A circuits."	B. El-Kareh et al., "A 5V complementary -SiGe BiCMOS technology for high-speed precision analog circuits." Date unknown									
/DN/	D. V. Singh et al., "Effect of band alignment and density of states on the collector current in p-Si/										
/DN/	n-Si _{1-y} C _y /p-Si HBTs," IEEE Transactions on Electron Devices, Vol. 50, No. 2, February 2003, pp. 425-32.										
Examiner (To	be assigned) /David	d Nhu/	Date: 09/02/2	010							

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Receipt date: 05/30/2006

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Sheet 2 of 2 IAP20 Rec'd PCT/PTO 30 MAY 2006

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TRANSLATION YES/NO OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.) 7 Y. Chyan et al., "A 50-GHz 0.25\(\mu\) implanted-base high-energy implanted-collector complementary modular BiCMOS (HEICBIC) technology for low-power wireless-communication VLSIs," IEEE BCTM 7.3, 1998, pp. 128-131. Date unknown 8 D. L. Harame et al., "55 GHz polysilicon-emitter graded SiGe-base PNP transistors," 1991, p. 71. 9 T. Onai et al., "Self-aligned complementary bipolar technology for low-power dissipation and ultra-high-speed LSIs," IEEE Transactions on Electron Devices, Vol. 42, No. 3, March 1995, pp. 413-418. 10 S. J. Jeng et al., "A 210-GHz fr SiGe HBT with a non-self-aligned structure," IEEE Electron Device Letters, Vol. 22, No. 11, November 2001. 11 J. D. Cressler et al., "A high-speed complementary silicon bipolar technology with 12-fJ power-delay product," IEEE Electron Device Letters, Vol. 14, No. 11, November 1993, pp. 523-526.	/DN/		6,222,250	April 24, 2001	Gomi					
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